



ZX5T853G

100V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Features

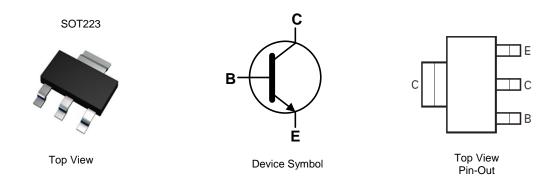
- BV_{CEO} > 100V
- I_C = 6A High Continuous Collector Current
- I_{CM} = 10A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 35mV
- $R_{SAT} = 36m\Omega$ at 6A for a Low Equivalent On-Resistance
- h_{FE} Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: ZX5T953G
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads;
 Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.112 grams (Approximate)

Applications

- Motor Driving
- Line Switching
- High Side Switches



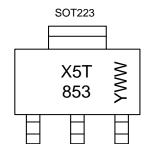
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZX5T853GTA	AEC-Q101	X5T853	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{ll} X5T~853 = Product~Type~Marking~Code\\ YWW = Date~Code~Marking\\ Y~or~\overline{Y} = Last~Digit~of~Year~(ex:~5=~2015)\\ WW~or~\overline{W}W = Week~Code~(01~53) \end{array}$



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	200	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	6	Α
Peak Pulse Current	I _{CM}	10	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3.0 24	W	
Linear Derating Factor	(Note 6)	P _D	1.6 12.8	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ heta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	$R_{ heta JL}$	10.5		
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

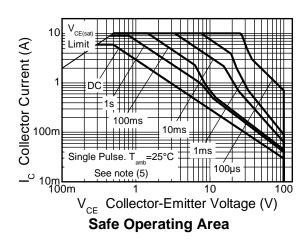
 6. Same as Note 5, except the device is surface mounted on 25mm x 25mm with 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

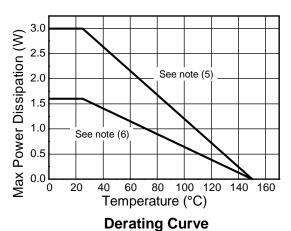
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

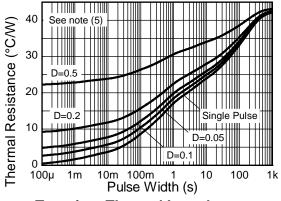
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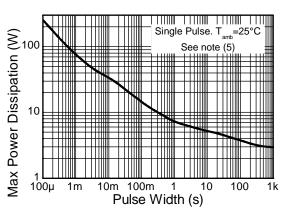


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

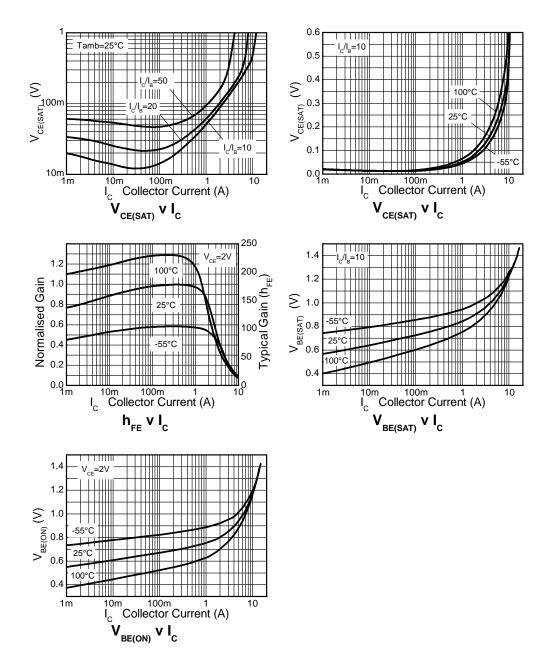
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	200	235	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	200	235	-	V	$I_C = 1\mu A$, RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	100	115	-	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	-	V	$I_E = 100\mu A$
Collector-Base Cut-Off Current	I _{CBO}	-	<1 -	20 0.5	nΑ μΑ	V _{CB} = 150V V _{CB} = 150V, T _A = +100°C
Collector-Emitter Cut-Off Current	l _{CER} R ≤ 1kΩ	-	-	20 0.5	nΑ μΑ	V _{CB} = 150V V _{CB} = 150V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	-	-	10	nA	$V_{EB} = 6V$
	h _{FE}	100	230	-		$I_C = 10$ mA, $V_{CE} = 2$ V
Static Forward Current Transfer Ratio (Note 9)		100	200	300		$I_C = 2A$, $V_{CE} = 2V$
Static Folward Current Transfer Ratio (Note 9)		30	60	-	-	$I_C = 5A$, $V_{CE} = 2V$
		10	20	-		$I_C = 10A, V_{CE} = 2V$
	V _{CE} (sat)	-	21	35		$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		-	50	65	mV	$I_C = 1A$, $I_B = 100mA$
Collector-Emilier Saturation Voltage (Note 9)		-	95	125	IIIV	$I_C = 2A$, $I_B = 100mA$
		-	180	220		$I_C = 5A$, $I_B = 500mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	-	1,020	1,120	mV	$I_C = 5A$, $I_B = 500mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	-	920	1,000	mV	$I_C = 5A$, $V_{CE} = 2V$
Output Capacitance (Note 9)	C_obo	-	26	-	pF	$V_{CB} = 10V. f = 1MHz$
Transition Frequency	f _T	-	130	-	MHz	V _{CE} = 10V, I _C = 100mA f = 50MHz
Switching Time	t _{on}	-	41	-	ns	$V_{CC} = 10V$, $I_C = 1A$
Owitering Time	t _{off}	-	1,010	-	113	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

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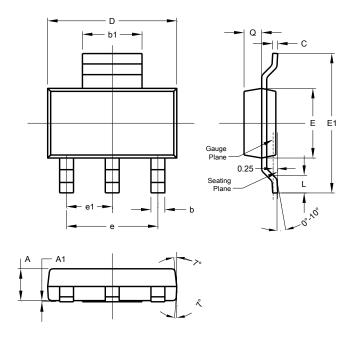
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

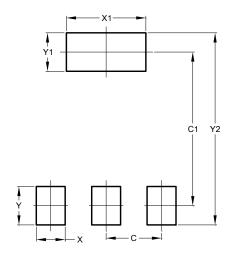
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Ø	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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